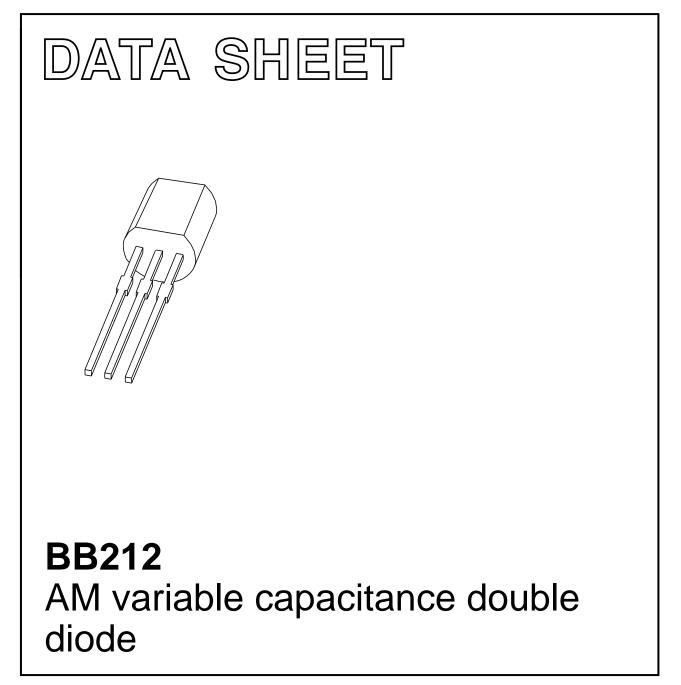
DISCRETE SEMICONDUCTORS



Product specification Supersedes data of April 1992 File under Discrete Semiconductors, SC01 1996 May 03



FEATURES

- Leaded plastic package
- C8: 19 pF; ratio: 29.

APPLICATIONS

- Electronic tuning in AM radio applications
- VCO.

DESCRIPTION

The BB212 is a variable capacitance double diode with a common cathode, fabricated in planar technology, and encapsulated in the TO-92 variant leaded plastic package.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	MIN.	MAX.	UNIT		
Per diode						
V _R	continuous reverse voltage –		12 V			
I _F	continuous forward current	-	100	mA		
T _{stg}	storage temperature		+100	°C		
Tj	operating junction temperature –55 +85 °C		°C			

PINNING

PIN	DESCRIPTION
1	anode (a1)
2	common cathode
3	anode (a2)

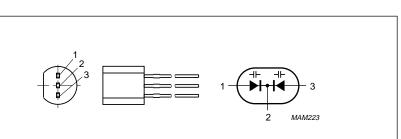


Fig.1 Simplified outline (TO-92 variant) and symbol.

BB212

Product specification

BB212

ELECTRICAL CHARACTERISTICS

 $T_i = 25 \ ^{\circ}C$; unless otherwise specified.

PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
•					•
reverse current	V _R = 10 V; see Fig.3	-	-	50	nA
	V_R = 10 V; T _j = 85 °C; see Fig.3	-	-	300	nA
diode series resistance	f = 500 MHz; note 1			2.5	Ω
diode capacitance	see Figs 2 and 4				
	V _R = 0.5 V; f = 1 MHz	500	-	620	pF
	V _R = 3 V; f = 1 MHz	140	-	280	pF
	V _R = 5.5 V; f = 1 MHz	40	-	90	pF
	V _R = 8 V; f = 1 MHz	-	-	22	pF
capacitance ratio	f = 1 MHz	22.5	-	-	
	reverse current diode series resistance diode capacitance	$\label{eq:reverse current} \begin{array}{c} V_R = 10 \ \text{V}; \ \text{see Fig.3} \\ \hline V_R = 10 \ \text{V}; \ \text{T}_j = 85 \ ^{\circ}\text{C}; \ \text{see Fig.3} \\ \hline \text{diode series resistance} & f = 500 \ \text{MHz}; \ \text{note 1} \\ \hline \text{diode capacitance} & \text{see Figs 2 and 4} \\ V_R = 0.5 \ \text{V}; \ f = 1 \ \text{MHz} \\ V_R = 3 \ \text{V}; \ f = 1 \ \text{MHz} \\ V_R = 5.5 \ \text{V}; \ f = 1 \ \text{MHz} \\ V_R = 8 \ \text{V}; \ f = 1 \ \text{MHz} \\ \end{array}$	$\begin{array}{c} \mbox{reverse current} & V_R = 10 \ \mbox{V}; \ \mbox{see Fig.3} & - \\ \hline V_R = 10 \ \mbox{V}; \ \mbox{T}_j = 85 \ \ \mbox{°C}; \ \mbox{see Fig.3} & - \\ \hline \mbox{diode series resistance} & f = 500 \ \mbox{MHz}; \ \mbox{note 1} & \\ \hline \mbox{diode capacitance} & \mbox{see Figs 2 and 4} & \\ V_R = 0.5 \ \ \mbox{V}; \ \mbox{f} = 1 \ \ \mbox{MHz} & 500 \\ V_R = 3 \ \ \ \mbox{V}; \ \mbox{f} = 1 \ \ \ \mbox{MHz} & 140 \\ V_R = 5.5 \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \$	$ \begin{array}{c c} reverse \ current & V_R = 10 \ V; \ see \ Fig.3 & - & - \\ \hline V_R = 10 \ V; \ T_j = 85 \ ^\circ C; \ see \ Fig.3 & - & - \\ \hline diode \ series \ resistance & f = 500 \ MHz; \ note \ 1 & & \\ \hline diode \ capacitance & see \ Figs \ 2 \ and \ 4 & & \\ V_R = 0.5 \ V; \ f = 1 \ MHz & 500 \ - \\ V_R = 3 \ V; \ f = 1 \ MHz & 140 \ - \\ V_R = 5.5 \ V; \ f = 1 \ MHz & 40 \ - \\ V_R = 8 \ V; \ f = 1 \ MHz & - \\ \end{array} $	$ \begin{array}{c c c c c c c c c c c c c c c c c c c $

Note

1. V_R is the value at which $C_d = 500 \text{ pF}$.

MATCHING PROPERTIES

The capacitance of the two diodes in their common package may differ within certain limits. The total, relative capacitance difference between the two diodes in one package may be found in Fig.5. The anode a1 or a2 with the higher capacitance at $V_R = 3$ V, is identified by a white dot.

BASIC TOLERANCE

The relative deviation of the capacitance value at $V_R = 0.5$ V is maximum 3.5%.

$$k = \left| \frac{C_1 (0.5V) - C_2 (0.5 V)}{C_2 (0.5 V)} \right| = <3.5\%$$

ADDITIONAL TOLERANCE (see Fig.5)

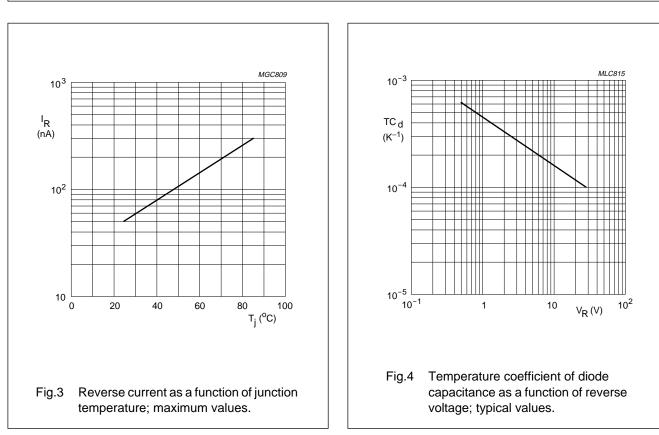
In the range of $V_R = 0.5$ V to 8 V the following additional tolerances are valid.

$$S = \left| \left(\frac{C_1}{C_2} \right) V_R - \left(\frac{C_1}{C_2} \right) 0.5 V \right|$$

 $\begin{array}{l} S < 2\% \mbox{ for } V_{R} = 0.5 \mbox{ to } 3 \mbox{ V} \\ S < 4\% \mbox{ for } V_{R} = 3 \mbox{ to } 5.5 \mbox{ V} \\ S < 6\% \mbox{ for } V_{R} = 5.5 \mbox{ to } 8 \mbox{ V}. \end{array}$

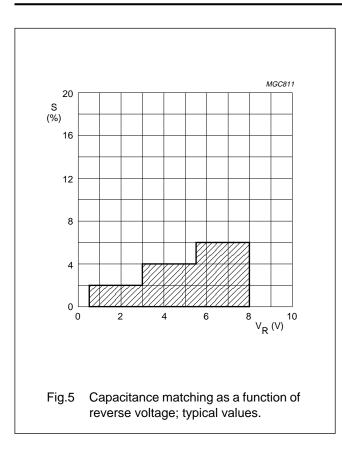
 C_1 is the capacitance of a1 when a1 > a2. C_1 is the capacitance of a2 when a2 > a1.

$f_{(p)}^{(q)}$ $f_{(p)}^{(q)$

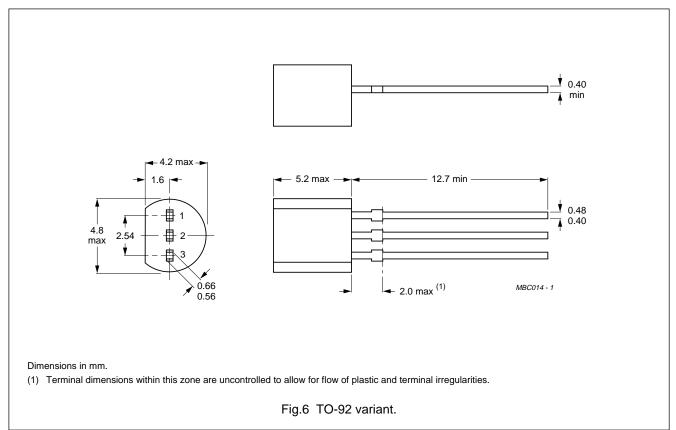


GRAPHICAL DATA

BB212



PACKAGE OUTLINE



DEFINITIONS

Data sheet status			
Objective specification	This data sheet contains target or goal specifications for product development.		
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published late		
Product specification	This data sheet contains final product specifications.		
Limiting values			
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.			
Application information			

Where application information is given, it is advisory and does not form part of the specification.

LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.

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